Contents

1	Electrical ratings
2	Electrical characteristics
	2.1 Electrical characteristics (curves)
3	Test circuits
4	Package mechanical data 11
5	Package mechanical data 20
6	Revision history



1 Electrical ratings

			Value		
Symbol	Parameter	TO-220FP I ² PAKFP	H ² PAK-2	TO-220	Unit
V_{DS}	Drain-source voltage		100		V
V _{GS}	Gate-source voltage		± 20		V
I _D ⁽¹⁾	Drain current (continuous) at $T_{C} = 25^{\circ}C$	46	120		А
I _D ⁽¹⁾	Drain current (continuous) at T _C =100°C	29	7	8	А
I _{DM} ⁽²⁾	Drain current (pulsed)	184	450		А
P _{TOT}	Total dissipation at $T_C = 25^{\circ}C$	35	250		W
dv/dt	Peak diode recovery voltage slope		22		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; $T_C = 25$ °C)	2500			V
E _{AS} ⁽³⁾	Single pulse avalanche energy		125		mJ
T _j T _{stg}	Operating junction temperature storage temperature	-	55 to 175		°C

Table 2.Absolute maximum ratings

1. Current limited by package.

2. Pulse width limited by safe operating area.

3. Starting Tj = 25 °C, I_D = 50 A, V_{DD} = 50 V for TO-220 and H²PAK-2; Starting Tj = 25 °C, I_D = 29 A, V_{DD} = 60 V for I²PAKFP and TO-220FP.

Table 3.Thermal data

			Value		
Symbol	Parameter	TO-220FP I ² PAKFP	H ² PAK-2	TO-220	Unit
Rthj-case	Thermal resistance junction-case	4.3	0.6	0.6	°C/W
Rthj-a	Thermal resistance junction-ambient	62.5		62.5	°C/W
Rthj-pcb ⁽¹⁾	Thermal resistance junction-pcb		35		°C/W

1. When mounted on FR-4 board, on 1inch², 2oz Cu.



2 Electrical characteristics

 $(T_{CASE} = 25 \degree C \text{ unless otherwise specified})$

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0, I _D = 250 μA	100	-		V
I _{DSS}	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 100 V$ $T_{C} = 25^{\circ}C$ $T_{C} = 125^{\circ}C$		-	10 100	μΑ μΑ
I _{GSS}	Gate body leakage current	$V_{DS} = 0, V_{GS} = \pm 20 V$		-	±200	nA
V _{GS(th)}	Gate threshold voltage	V_{DS} = V_{GS} , I_D = 250 μ A	2	-	4	V
B	Static drain-source on-	V _{GS} = 10 V, I _D = 23A TO-220FP and I²PAKFP		8	9.6	mΩ
R _{DS(on)}	resistance	V _{GS} = 10 V, I _D = 60 A H²PAK TO-220		7.8 8	9.3 9.6	11152

Table 4. On/off states

	2 y mainine					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{GS} = 0, V _{DS} = 25 V, f = 1 MHz	-	3305 373 23	-	pF pF pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 50 \text{ V}, I_D = 120 \text{ A},$ $V_{GS} = 10 \text{ V}$ (see <i>Figure 20</i>)	-	57 22 17	-	nC nC nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time	$V_{DD} = 50 \text{ V}, \text{ I}_{D} = 60 \text{ A}$		17		ns
t _r	Rise time	$R_{G} = 4.7 \ \Omega V_{GS} = 10 \ V$	_	38	_	ns
t _{d(off)}	Turn-off delay time	(see Figure 19,	-	52	-	ns
t _f	Fall time	Figure 24)		7.2		ns



Table 7.	Source drain diode					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD} I _{SDM} ⁽¹⁾	Source-drain current Source-drain current (pulsed)	For TO-220FP and I ² PAKFP	-		46 184	A A
I _{SD} I _{SDM} ⁽²⁾	Source-drain current Source-drain current (pulsed)	For TO-220, H ² PAK-2	-		120 450	A A
		I _{SD} =120 A, V _{GS} =0; for TO-220, H²PAK-2				
V _{SD} ⁽³⁾	Forward on voltage	I _{SD} =46 A, V _{GS} =0; for TO-220FP and I²PAKFP	-		1.5	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I _{SD} =120 A, di/dt = 100 A/μs, V _{DD} =80 V, Tj=150 °C (see <i>Figure 21</i>)	-	68 182 5.4		ns nC A

Table 7. Source drain diode

1. Pulse width limited by safe operating area

2. Pulse width limited by safe operating area

3. Pulsed: pulse duration = 300 μ s, duty cycle 1.5%



2.1 Electrical characteristics (curves)





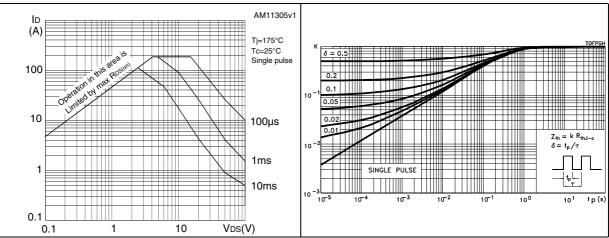
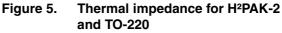
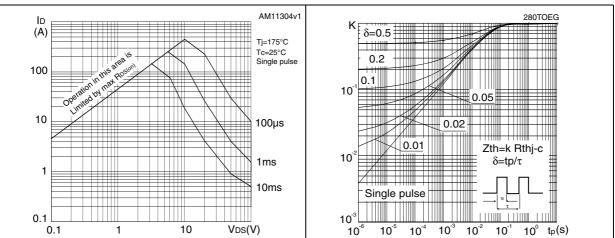


Figure 4. Safe operating area for H²PAK-2 and TO-220









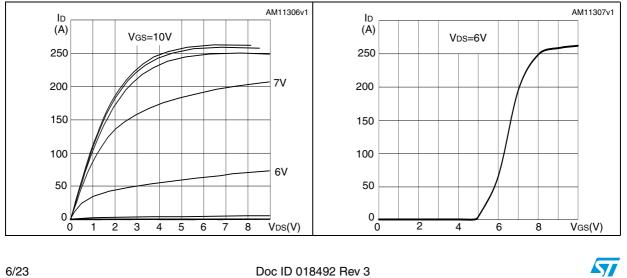


Figure 8. Static drain-source on-resistance for TO-220FP and I²PAKFP

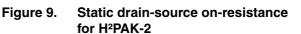


Figure 11. Normalized $B_{VDSS} \ vs$ temperature

Electrical characteristics

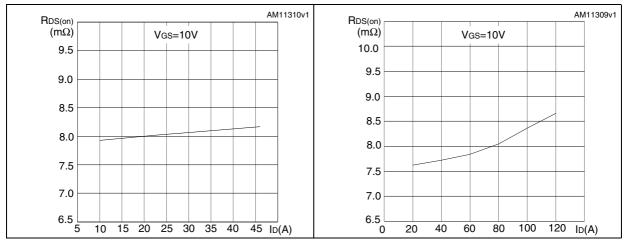
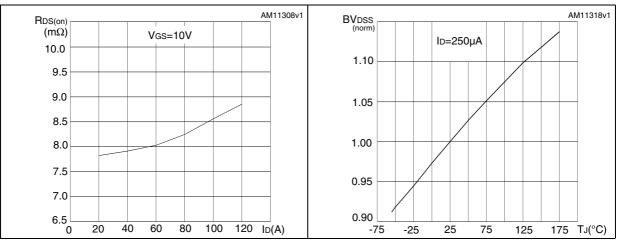
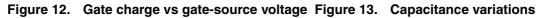


Figure 10. Static drain-source on-resistance for TO-220





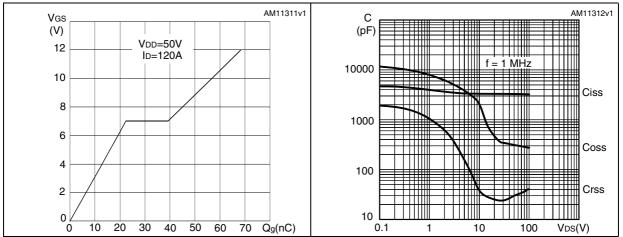
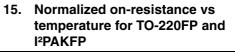


Figure 14. Normalized gate threshold voltage Figure 15. vs temperature



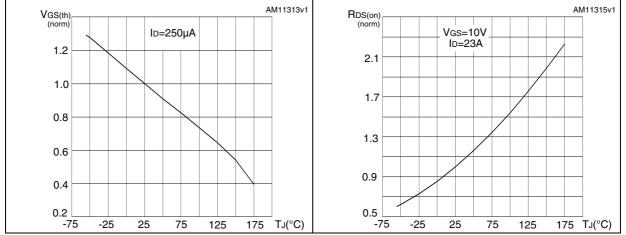
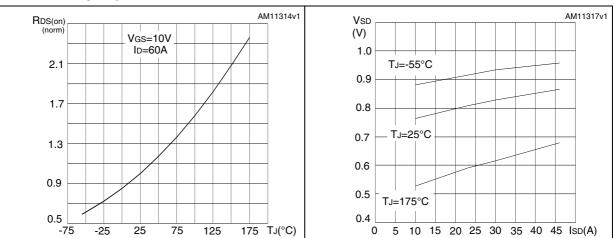


Figure 16. Normalized on resistance vs temperature for H²PAK-2 and TO-220

Figure 17. Source-drain diode forward characteristics for TO-220FP and I²PAKFP





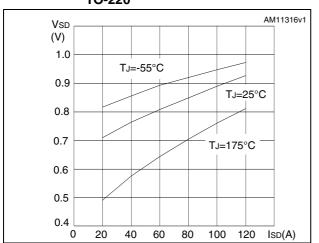


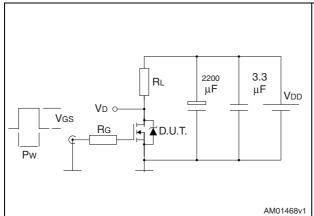
Figure 18. Source-drain diode forward characteristics for H²PAK-2 and TO-220



Figure 20. Gate charge test circuit

3 Test circuits

Figure 19. Switching times test circuit for resistive load



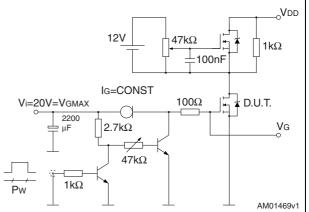
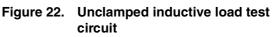
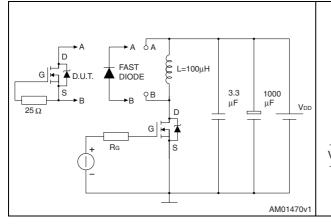


Figure 21. Test circuit for inductive load switching and diode recovery times





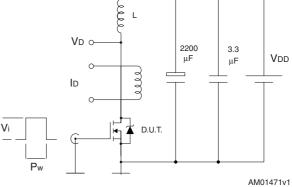
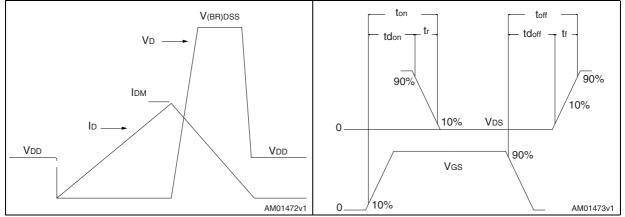




Figure 24. Switching time waveform





4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.



Dim		mm	
Dim.	Min.	Тур.	Max.
A	4.4		4.6
В	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
Н	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Table 8.TO-220FP mechanical data





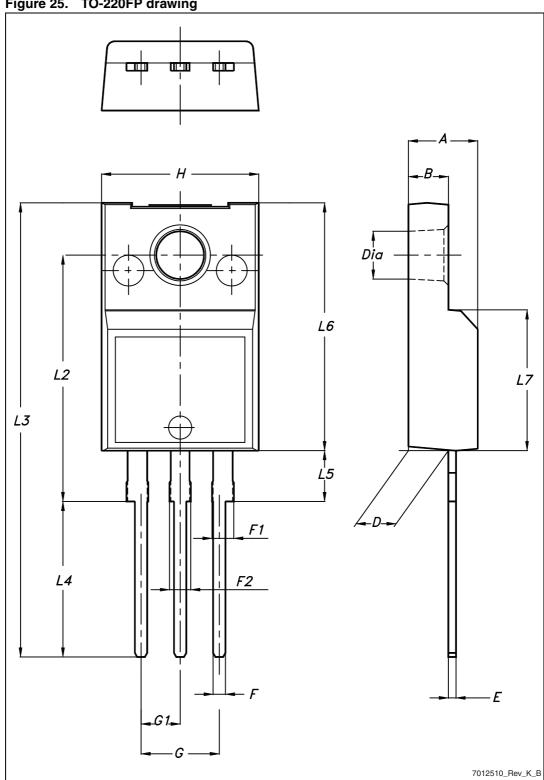


Figure 25. TO-220FP drawing



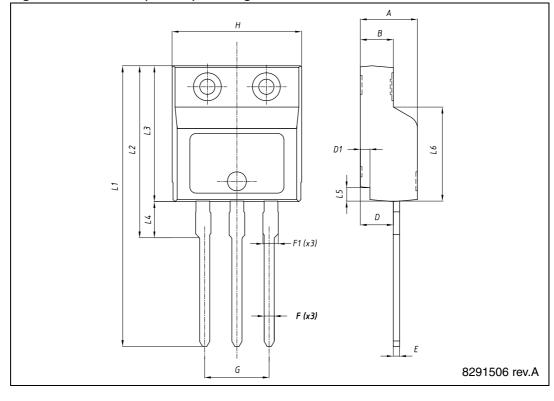
Dim		mm	
Dim.	Min.	Тур.	Max.
A	4.40		4.60
В	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95	-	5.20
Н	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25

 Table 9.
 I²PAKFP (TO-281) mechanical data

Figure 26. I²PAKFP (TO-281) drawing

7.30

L6



Doc ID 018492 Rev 3



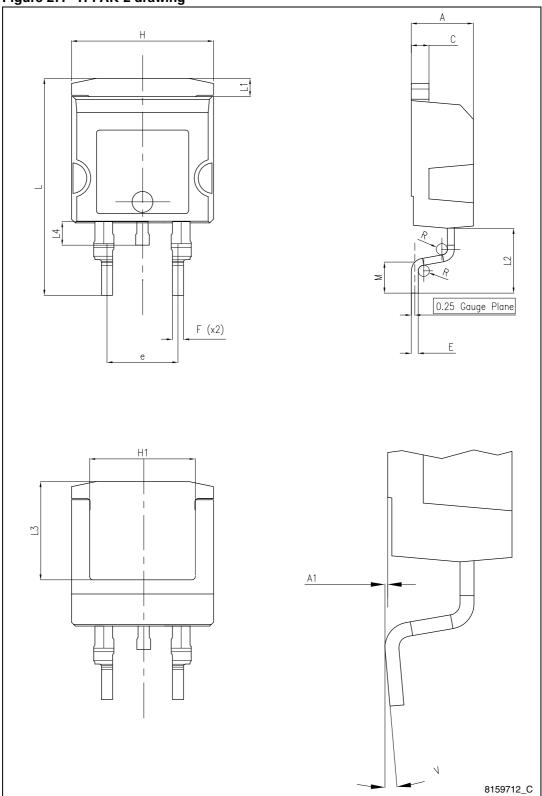
7.50

Dim		mm	
Dim.	Min.	Тур.	Max.
A	4.30		4.80
A1	0.03		0.20
С	1.17		1.37
е	4.98		5.18
E	0.50		0.90
F	0.78		0.85
Н	10.00		10.40
H1	7.40		7.80
L	15.30	-	15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
М	2.6		2.9
R	0.20		0.60
V	0°		8°

Table 10. H²PAK-2 mechanical data



Figure 27. H²PAK-2 drawing





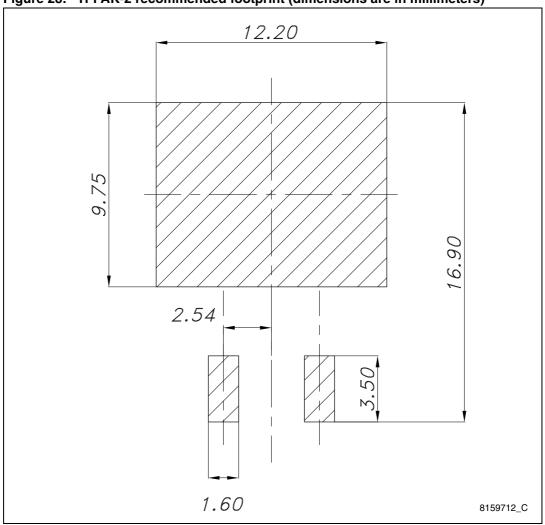


Figure 28. H²PAK-2 recommended footprint (dimensions are in millimeters)



Dim		mm	
Dim.	Min.	Тур.	Max.
А	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
С	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
е	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØР	3.75		3.85
Q	2.65		2.95

Table 11. TO-220 type A mechanical data



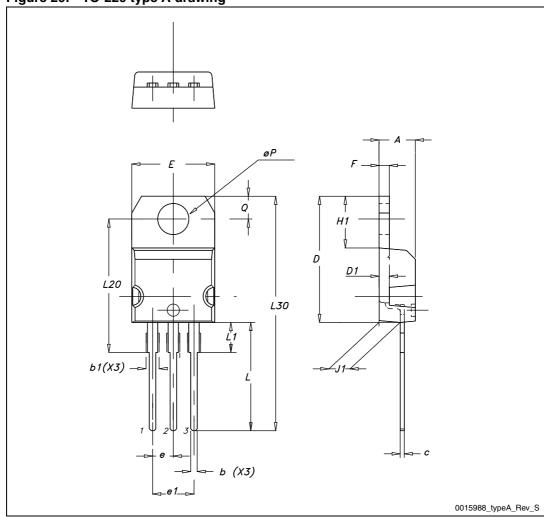


Figure 29. TO-220 type A drawing



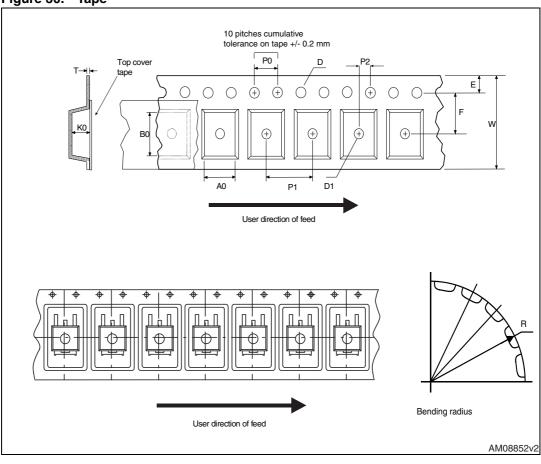
5 Package mechanical data

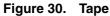
Таре			Reel			
Dim	mm		Dim	mm		
Dim. —	Min.	Max.	— Dim. –	Min.	Max.	
A0	10.5	10.7	А		330	
B0	15.7	15.9	В	1.5		
D	1.5	1.6	С	12.8	13.2	
D1	1.59	1.61	D	20.2		
Е	1.65	1.85	G	24.4	26.4	
F	11.4	11.6	Ν	100		
K0	4.8	5.0	Т		30.4	
P0	3.9	4.1				
P1	11.9	12.1		Base qty 1000		
P2	1.9	2.1		Bulk qty 1000		
R	50					
Т	0.25	0.35				
W	23.7	24.3				

Table 12. H²PAK-2 tape and reel mechanical data

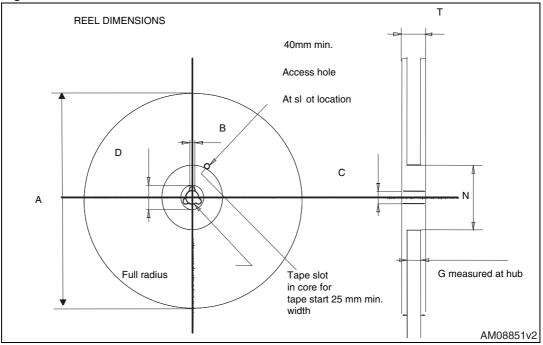
20/23













6 Revision history

Table 13.	Document revision history
-----------	---------------------------

Date	Revision	Changes
24-Feb-2011	1	First version.
07-May-2012	2	Added <i>Section 2.1: Electrical characteristics (curves).</i> Minor text changes.
07-Nov-2012	3	Added new device in I ² PAKFP and updated the document accordingly. Updated <i>Section 4: Package mechanical data</i> .

22/23



Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2012 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

